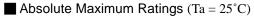
LN52

GaAs Infrared Light Emitting Diode

For optical control systems

Features

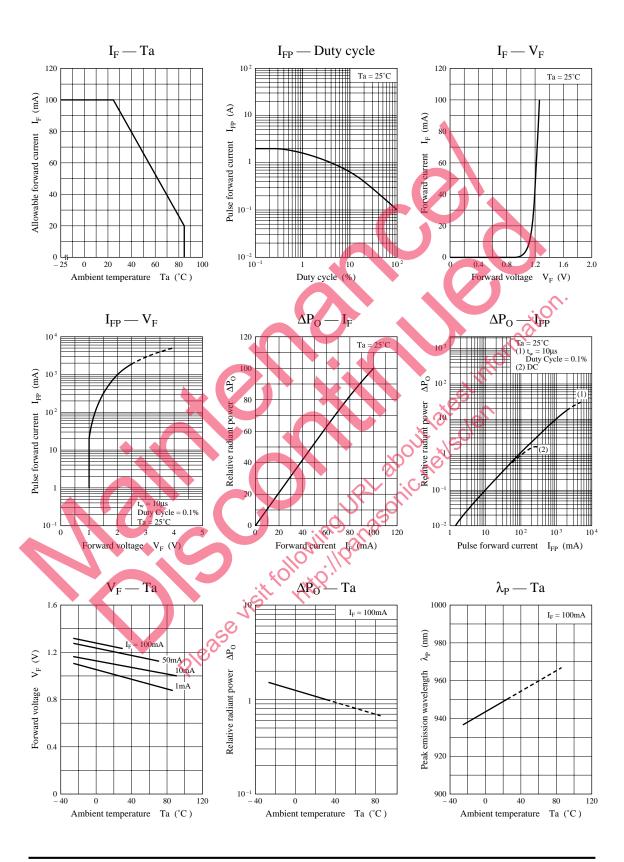
- High-power output, high-efficiency : $P_0 = 6 \text{ mW (typ.)}$
- Wide directivity, matched for external optical systems : $\theta = 100$ deg.
- Infrared light emission close to monochromatic light : $\lambda_P = 950 \text{ nm}$
- Optimum for mesuring instruments and control equipments in conbination with silicon photodetectors

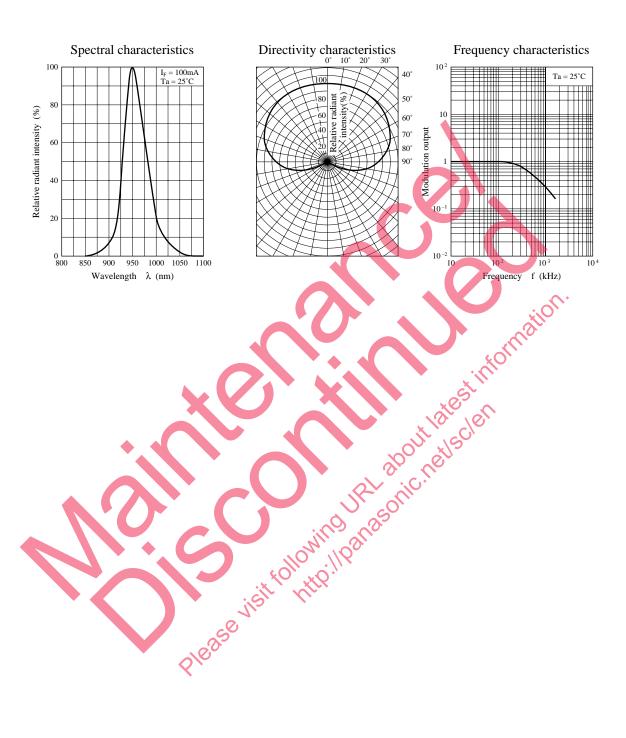


| Parameter | Symbol | Ratings | Unit |
|-------------------------------|------------------|-------------|------|
| Power dissipation | P_{D} | 160 | mW |
| Forward current (DC) | I_{F} | 100 | mA |
| Pulse forward current | I_{FP}^* | 2 | A |
| Reverse voltage (DC) | V_{R} | 3 | V |
| Operating ambient temperature | T_{opr} | -25 to +85 | °C |
| Storage temperature | T _{stg} | -30 to +100 | °C |

Unit : mm -ø0.45±0.05 1: Cathode 2: Anode

| Absolute Maximum Rati | ngs (Ta = | 25°C) | | | | 1254100 | <i>U</i> . |
|--|--|--|---------------------------|---------|-------------------------------|------------|---------------------------|
| Parameter | Symbol | Ratings | Unit | | - | 2.54±0.25 | 1: Cathode |
| Power dissipation | P_{D} | 160 | mW | | | Mo | 2: Anode |
| Forward current (DC) | I_{F} | 100 | mA | | ٤٥ | <i>y</i> , | |
| Pulse forward current | I_{FP}^* | 2 | A | | 110. | | |
| Reverse voltage (DC) | V_{R} | 3 | V | . 0 | S | | |
| Operating ambient temperature | Topr | -25 to +85 | °C | Silver | 100 | | |
| Storage temperature | T _{stg} | -30 to +100 | °C | J. J. | Cl | | |
| * f = 100 Hz, Duty cycle = 0.1 % | 9 | | | 20 ×16 |) | | |
| | | _ | | | | | |
| ■ Electro-Optical Charact | | | A V °C °C °C °C onditions | 1 | | | Unit |
| Parameter | Symbol | 10 | onditions | min 3.5 | typ 6 | max | Unit mW |
| Parameter Radiant power | Symbol | | onditions | min | typ | | |
| Parameter | Symbol | $I_{\rm F}$ = 100mA | onditions | min | typ 6 | | mW |
| Parameter Radiant power Peak emission wavelength | Symbol P _O λ_P | $I_F = 100 \text{mA}$ $I_F = 100 \text{mA}$ | onditions | min | typ 6 950 | | mW nm |
| Parameter Radiant power Peak emission wavelength Spectral half band width | $\begin{array}{c} \text{Symbol} \\ P_{O} \\ \lambda_{P} \\ \Delta\lambda \end{array}$ | $I_F = 100 \text{mA}$ $I_F = 100 \text{mA}$ $I_F = 100 \text{mA}$ | onditions | min | typ 6 950 50 | max | mW nm nm |
| Parameter Radiant power Peak emission wavelength Spectral half band width Forward voltage (DC) | $\begin{array}{c} \text{Symbol} \\ P_{O} \\ \lambda_{P} \\ \Delta \lambda \\ V_{F} \end{array}$ | $I_F = 100 \text{mA}$ $I_F = 100 \text{mA}$ $I_F = 100 \text{mA}$ $I_F = 100 \text{mA}$ | onditions | min | typ 6 950 50 | max 1.6 | mW nm nm |
| Parameter Radiant power Peak emission wavelength Spectral half band width Forward voltage (DC) Reverse current (DC) | $\begin{array}{c} \text{Symbol} \\ P_{O} \\ \lambda_{P} \\ \Delta \lambda \\ \text{VF} \\ I_{R} \end{array}$ | $I_F = 100 \text{mA}$ $I_F = 100 \text{mA}$ $I_F = 100 \text{mA}$ $I_F = 100 \text{mA}$ $V_R = 3V$ $V_R = 0V, \text{ f}$ | onditions = 1MHz | min | typ 6 950 50 1.25 | max 1.6 | mW nm nm V μA |
| Parameter Radiant power Peak emission wavelength Spectral half band width Forward voltage (DC) Reverse current (DC) Capacitance between pins | $\begin{array}{c} \text{Symbol} \\ P_O \\ \lambda_P \\ \Delta \lambda \\ V_F \\ C_t \end{array}$ | $I_F = 100 \text{mA}$ $I_F = 100 \text{mA}$ $I_F = 100 \text{mA}$ $I_F = 100 \text{mA}$ $V_R = 3V$ | onditions = 1MHz | min | typ 6 950 50 1.25 | max 1.6 | mW nm nm V µA pF |







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GaAs powder and vapor are hazardous to human health if inhaled or ingested. Do not burn, destroy, cut, cleave off, or chemically dissolve the product. Follow related laws and ordinances for disposal. The product should be excluded from general industrial waste or household garbage.

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